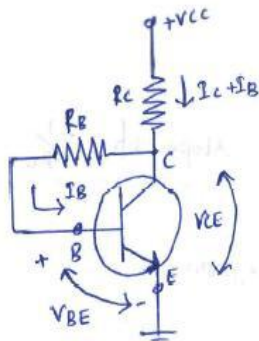




Topic 1.4 : Collector-to-base Bias configuration

2. Collector to Base Bias / Biasing with Feedback Resistor



- * It's an improvement over the fixed bias method
- * The resistor is connected b/w the base & the collector of the transistor. Hence, the circuit is called collector to base bias circuit.
- * Thus I_B flows through R_B & $(I_C + I_B)$ flows through the R_C .

DC Analysis

* For DC $f = 0$

$$X_C = \frac{1}{2\pi f C} = \frac{1}{0} = \infty$$

Collector Current I_C

- * Apply KVL to the base-emitter circuit

$$V_{CC} - (I_B + I_C)R_C - I_B R_B - V_{BE} = 0$$

$$V_{CC} - (\beta + 1)I_B R_C - I_B R_B - V_{BE} = 0$$

$$V_{CC} - I_B ((\beta + 1)R_C + R_B) - V_{BE} = 0$$

$$V_{CC} - V_{BE} = I_B ((\beta + 1)R_C + R_B)$$

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)R_C}$$

- * If there is a change in β due to piece to piece variation b/w Transistors, then I_C tends to increase. As the result voltage drop across R_C increases.
- * The supply voltage V_{CC} is constant, due to increase in $I_C R_C$, V_{CE} decreases. Due to reduction in V_{CE} , I_B decreases. This I_B reduction in lead to increase I_C .



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w.k.T $I_B = \frac{I_C}{\beta} \Rightarrow I_C = \beta I_B$

$$I_C = \beta \left[\frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)R_C} \right]$$

Collector Emitter Voltage V_{CE}

* Apply KVL to the collector - Emitter circuit

$$V_{CC} - (I_B + I_C)R_C - V_{CE} = 0$$

$$V_{CE} = V_{CC} - (I_B + I_C)R_C$$

Load Line Analysis

* Apply KVL to the collector - Emitter circuit

$$V_{CC} - (I_B + I_C)R_C - V_{CE} = 0$$

* Assume $I_B + I_C \approx I_C$

$$V_{CC} - I_C R_C - V_{CE} = 0$$

$$I_C = -\frac{1}{R_C} V_{CE} + \frac{V_{CC}}{R_C}$$

* The equation represents a DC load line with slope of $-\frac{1}{R_C}$ & y-intercept

$$\frac{V_{CC}}{R_C}$$

* When $I_C = 0$ i.e. Transistor is in cut-off region

$$V_{CE} = V_{CC}$$

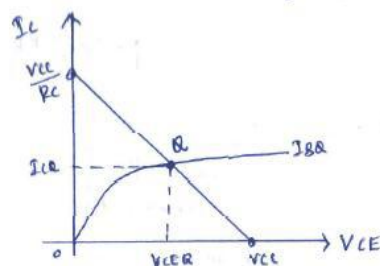
* When $V_{CE} = 0$ i.e. Transistor is in saturation region

$$I_C = \frac{V_{CC}}{R_C}$$

* Thus the 2 end points are $(V_{CC}, 0)$ & $(0, \frac{V_{CC}}{R_C})$. by joining the 2 end points DC load line is drawn.

* From Base - Emitter circuit

$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)R_C}$$



The saturation current for the circuit is $I_{C \text{ sat}} = \frac{V_{CC}}{R_C}$



Stability Factors

S:

* Apply KVL to the base-emitter junction

$$V_{CC} = I_C R_C + I_B (R_C + R_B) + V_{BE}$$

* When I_B changes by ∂I_B & I_C changes by ∂I_C There is no effect on V_{CC} & V_{BE}

* So the equation becomes

$$0 = \partial I_C R_C + \partial I_B (R_C + R_B) + 0$$

$$\partial I_B (R_C + R_B) = -\partial I_C R_C$$

$$\frac{\partial I_B}{\partial I_C} = -\frac{R_C}{R_C + R_B} \quad \text{--- (1)}$$

* substitute (1) in S

$$S = \frac{1 + \beta}{1 - \beta \left(\frac{\partial I_B}{\partial I_C} \right)} = \frac{1 + \beta}{1 - \beta \left(-\frac{R_C}{R_C + R_B} \right)}$$

$$S = \frac{1 + \beta}{1 + \beta \left(\frac{R_C}{R_C + R_B} \right)}$$

* The collector-base bias circuit is having lesser stability factor than fixed bias circuit.

* Hence the circuit provides better stability than fixed bias circuit.

S':

$$S' = \frac{-\beta}{R_B + (1 + \beta)R_C}$$

S'':

$$S'' = \frac{I_C}{\beta} \left(\frac{S}{1 + \beta} \right)$$